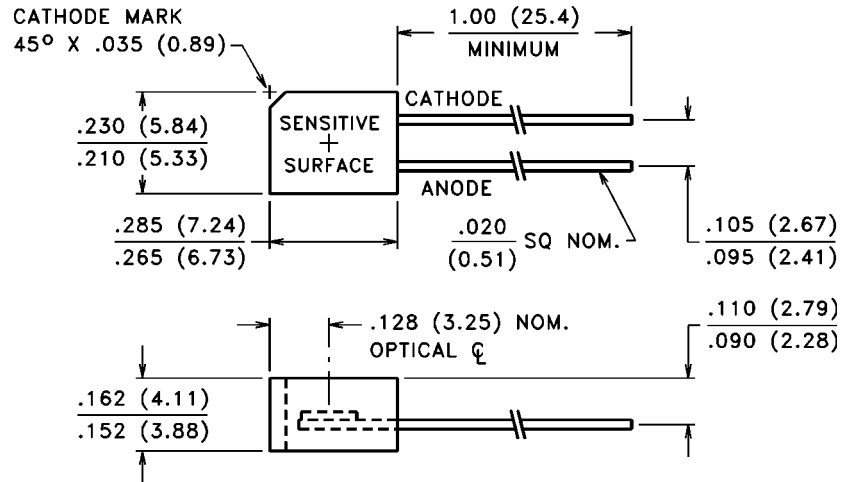




**PACKAGE DIMENSIONS** inch (mm)



CASE 52 FLAT SIDELOOKER  
CHIP ACTIVE AREA: .012 in<sup>2</sup> (7.45 mm<sup>2</sup>)

**PRODUCT DESCRIPTION**

Planar silicon photodiode in a molded plastic side-looker package. The package material is clear. These diodes exhibit low dark current and fast speed of response.

**ABSOLUTE MAXIMUM RATINGS**

Storage Temperature: -40°C to 100°C  
Operating Temperature: -40°C to 100°C

**RoHS Compliant**



**ELECTRO-OPTICAL CHARACTERISTICS @ 25°C** (See also VTP curves, pages 45-46)

SYMBOL	CHARACTERISTIC	TEST CONDITIONS	VTP100CH			UNITS
			Min.	Typ.	Max.	
I <sub>SC</sub>	Short Circuit Current	H = 100 fc, 2850 K	50	70		μA
TC I <sub>SC</sub>	I <sub>SC</sub> Temperature Coefficient	2850 K		.20		%/°C
V <sub>OC</sub>	Open Circuit Voltage	H = 100 fc, 2850 K		350		mV
TC V <sub>OC</sub>	V <sub>OC</sub> Temperature Coefficient	2850 K		-2.0		mV/°C
I <sub>D</sub>	Dark Current	H = 0, VR = 10 V			30	nA
R <sub>SH</sub>	Shunt Resistance	H = 0, V = 10 mV		.25		GΩ
C <sub>J</sub>	Junction Capacitance	H = 0, V = 3 V			50	pF
Re	Responsivity	940 nm		.050		A/(W/cm <sup>2</sup> )
S <sub>R</sub>	Sensitivity	@ Peak		.55		A/W
λ <sub>range</sub>	Spectral Application Range		400		1150	nm
λ <sub>p</sub>	Spectral Response - Peak			925		nm
V <sub>BR</sub>	Breakdown Voltage		30	140		V
θ <sub>1/2</sub>	Angular Resp. - 50% Resp. Pt.			±70		Degrees
NEP	Noise Equivalent Power			9.0 x 10 <sup>-14</sup> (Typ.)		W/√Hz
D*	Specific Detectivity			3.0 x 10 <sup>12</sup> (Typ.)		cm√Hz/W